BROADBAND POWER AMPLIFIER
ABP0060-01-2326

Features:

- Octave bandwidth, specification from 5~600MHz
- Low noise figure, high gain with good gain flatness
- Low VSWR, unconditional stable
- SMA female connector I/O
- Single DC power supply
- Operating temperature -40~+75°C, storage temperature -55~+125°C

General Description

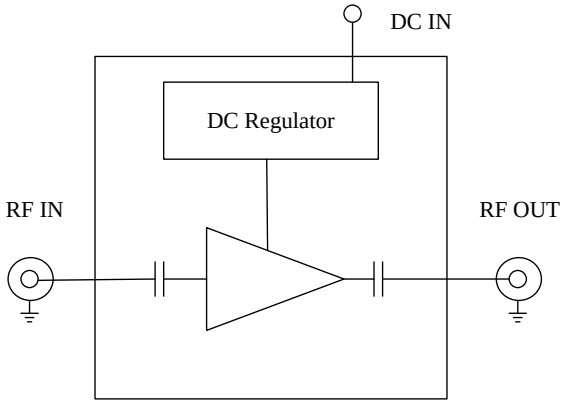
ABP0060-01-2326 is a single stage E-pHEMT based broadband power amplifier module operating in the frequency of 5 to 600MHz and provide +26dBm typical output P-1dB power with 23dB of small signal gain. The amplifier requires only a single positive DC power supply, its built-in DC voltage regulator allows for different DC voltage supply application. This amplifier is ideal for telecommunication infrastructures, microwave radio, test instrumentation and military applications.

Electrical Specifications

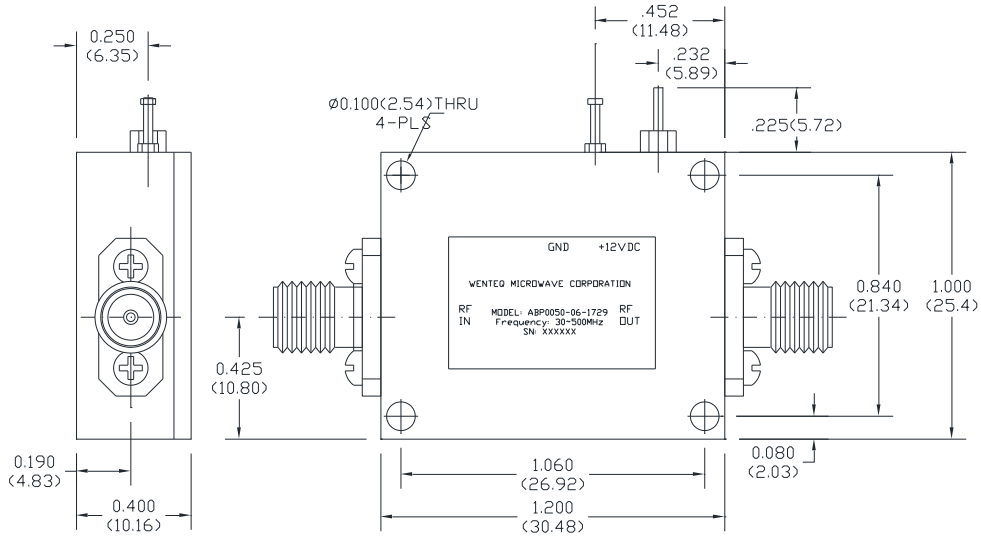
Parameters	Units	Specifications		
		Minimum	Typical	Maximum
Frequency Range	MHz	5		600.0
P-1dB Compression Point	dBm	+25.0	+26.0	
Output IP3	dBm	+40.0	+44.0	
Nominal SS Gain @25°C	dB	20.0	23.0	26.0
Gain flatness over 5~600MHz	dB		+/-1.5	+/-1.75
Gain Variation over temperature	dB		+/-0.4	+/-0.5
Noise Figure (above 10MHz)	dB		1.5	2.0
Input VSWR	-		1.5:1	2.0:1
Output VSWR	-		1.5:1	2.0:1
Reverse Isolation	dB	23.0		
Spurious	dBc			-60,0
Operating Temperature	°C	-40.0		+75.0
Survival Temperature	°C	-55.0		+125.0
DC Voltage	V	+11.0	+12.0	+13.0
DC Supply Current	mA	200.0	250 mA	300.0
In/Out connectors		50 ohm SMA female		
Size	inches	1.2x1.0x0.4		

138 W Pomona Ave, Monrovia, CA 91016
Phone: (626) 305-6666, Fax: (626) 602-3101, sales@wenteq.com, www.wenteq.com

Functional Diagram



Mechanical Structure:



Note: All units in inches (mm).

Housing Material and Surface Finish:

Body and cover material: aluminum
Surface finish: nickel plated
Connector material: Copper
Connector surface finish: gold plated

Absolute Maximum Ratings

DC Voltage	+13V
RF Input Power	+16dBm
Storage Temperature	-55~+125°C
Operating Temperature	-40~+75°C